

# Monolithic Amplifier

5 to 1500 MHz

### PGA-122-75+

 $\square$  Mini-Circuits 75 $\Omega$ 

#### THE BIG DEAL

- High IP3, +43 dBm typ. at 0.5 GHz
- Gain, 15.6 dB typ. at 0.5 GHz
- High P<sub>OUT</sub>, P1dB +73.1 dBmV typ. at 0.5 GHz
- Low Noise Figure, 2.9 dB at 0.5 GHz
- Usable over 5-2000 MHz



Generic photo used for illustration purposes only CASE STYLE: DF782

+RoHS Compliant The +Suffix identifies RoHS Compliance. See our website for methodologies and qualifications

#### **APPLICATIONS**

- CATV, DOCSIS 3.1
- GPON
- MOCA
- DBS

#### **PRODUCT OVERVIEW**

PGA-122-75+ (RoHS compliant) is an advanced wideband amplifier fabricated using E-PHEMT technology and offers extremely high dynamic range over a broad frequency range with low noise figure and flat gain. Lead finish is SnAgNi. It has repeatable performance from lot to lot and is enclosed in a SOT-89 package for very good thermal performance.

#### **KEY FEATURES**

Feature	Advantages
Broad Band: 0.04 to 1.5 GHz	0.04 to 1.5 GHz bandwidth covers primary CATV applications such as DOCSIS 3.1
Application circuit for 5 to 2000 MHz available	Supports bandwidth requirements for upstream CATV applications. See application note AN-60-087. Recommend Evaluation Board, TB-885+
High IP3 Versus DC power Consumption: +43 dBm typical at 0.5 GHz	The PGA-122-75+ matches industry leading IP3 performance relative to device size and power consumption. The combination of the design and E-PHEMPT structure provides enhanced linearity over a broad frequency range as evidence in the IP3 being typically 15-20 dB above the P 1dB point. This feature makes this amplifier ideal for use in CATV applications.
High IP2, +54 dBm at 0.5 GHz	Suppresses second order product on wideband applications such as CATV
Low Noise Figure, 2.9 dB at 0.5 GHz	Low noise figure performance in combination with the high output IP3 results in high dynamic range.
Excellent CSO/CTB* CSO, -59 dBc CTB, -80 dBc Measured at channel 78	Competitive performance at lower current and supply voltage.

\*78 channels flat, 30 dBmv/channel at output, 6 MHz channel spacing.

REV. A ECO-011959 PGA-122-75+ MCL NY 240807

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FLAT GAIN, HIGH DYNAMIC RANGE

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75Ω 5 to 1500 MHz

#### ELECTRICAL SPECIFICATIONS<sup>1</sup> AT +25°C, 75Ω AND +9V UNLESS NOTED OTHERWISE

Parameter	Condition	Vd=+9V			Vd=+8V	
Parameter	(GHz)	Min.	Тур.	Max.	Тур.	Units
Frequency Range		0.04		1.5	0.04-1.5	GHz
	0.04	_	15.5	_	15.5	
	0.5	_	15.6	_	15.6	
Gain	1.0	14.0	15.5	17.1	15.5	dB
	1.25	_	15.4	_	15.3	
	1.5	_	15.1	_	15.0	
Gain Flatness Over	0.04-1.25		±0.1		±0.1	dB
	0.04		17.8		17.6	
	0.5		21.2		20.8	
Input Return Loss	1.0		18.7		18.0	dB
	1.25		16.1		15.9	
	1.5		14.2		13.8	
	0.04		19.8		20.2	
	0.5		24.3		24.1	
Output Return Loss	1.0		16.4		16.7	dB
	1.25		13.0		13.0	
	1.5		10.0		9.8	
Reverse Isolation	1.0		21.0		21.0	dB
	0.04		23.4 (72.2)		22.4 (71.2)	dBm (dBmV)
	0.5		24.3 (73.1)		23.3 (72.1)	
Output Power @1dB Compression	1.0		23.8 (72.6)		23.1 (71.9)	
	1.25		23.3 (72.1)		22.3 (71.1)	
	1.5		22.8 (71.6)		21.6 (70.4)	
	0.04		+43.3		+42.3	
	0.5		+43.2		+43.6	
Output IP3	1.0		+41.4		+39.9	dBm
	1.25		+38.8		+37.0	
	1.5		+37.9		+35.4	
	0.04		+59.5		+56.9	
	0.5		+54.9		+53.0	
Output IP2 <sup>2</sup>	1.0		+58.5		+57.5	dBm
	1.25		+52.2		+50.1	
	1.5		+49.4		+47.2	
	0.04		2.9		3.0	
	0.5		2.9		2.8	
Noise Figure	1.0		2.8		2.9	dB
-	1.25		3.0		2.9	
	1.5		3.0		3.2	
Device operating voltage		+8.5	+9.0	+9.5	+8.0	V
Device operating current		_	115	140	102	mA
Device current variation vs temperature <sup>4</sup>			22		25	µA°/C
Device current variation vs voltage			0.0146		0.0146	mA/mV
Thermal resistance, junction-to-ground lead <sup>3</sup>			30		30	°C/W

1. Measured on Mini-Circuits Characterization Eval board TB-859+. See Characterization Test Circuit (Fig. 1)

2. Output IP2 measured at sum frequency of the two tones (f meas= f1+f2).

Junction to ground lead.
(Current at 85°C - Current at -45°C)/130

#### **ABSOLUTE MAXIMUM RATINGS<sup>5</sup>**

Parameter	Ratings		
Operating Temperature (ground lead)	-40°C to +85°C		
Storage Temperature	-65°C to +150°C		
Operating Current at +9.0V	167 mA		
Power Dissipation	1.5 W		
Input Power (CW)	+20 dBm over 40-1200 MHz, and +24 dBm over 1200-1500 MHz (5 minutes) +17 dBm over 40-1200 MHz, and +20 dBm over 1200-1500 MHz (continuous)		
DC Voltage on Pin 3	+11 V		

5. Permanent damage may occur if any of these limits are exceeded. Electrical maximum ratings are not intended for continuous normal operation.

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75Ω 5 to 1500 MHz

#### SIMPLIFIED SCHEMATIC AND PIN DESCRIPTION



Function	Pin Number	Description
RF-IN	1	RF input pin. This pin requires the use of an external DC blocking capacitor chosen for the frequency of operation.
RF-OUT and DC-IN	3	RF output and bias pin. DC voltage is present on this pin; therefore a DC blocking capacitor is necessary for proper operation. An RF choke is needed to feed DC bias without loss of RF signal due to the bias connection, as shown in "Recommended Application Circuit", Fig. 2
GND	2,4	Connections to ground. Use via holes as shown in "Suggested Layout for PCB Design" to reduce ground path inductance for best performance.

\*Enhanced mode pseudomorhic High Electron Mobility Transistor.

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#### **CHARACTERIZATION TEST CIRCUIT**



Fig 1. Block Diagram of Test Circuit used for characterization. (DUT tested on Mini-Circuits Characterization Eval board TB-859+) Gain, Return loss, Output power at 1dB compression (P1 dB), output IP3 (OIP3), output IP2 (OIP2) and noise figure measured using Agilent's N5242A PNA-X microwave network analyzer.

Conditions:

- 1. Gain and Return loss:  $P_{IN}$ = -25dBm
- 2. Output IP3 (OIP3): Two tones, spaced 1 MHz apart, 5 dBm/tone at output.
- 3. Output IP2 (OIP2): Two tones, spaced 11 MHz apart, 5 dBm/tone at output.

#### **RECOMMENDED APPLICATION CIRCUIT (TB-850+)**



COMPONENT	VALUE	SIZE	
DUT	PGA-122-75+	-	
C1	1000 pF		
C2	120 pF	0402	
C3	100 pF		
C4	10000 pF		
C5	10 uF, 25V	1206	
D1	Zener Diode 5.6V ONSEMI MMSZ4690T1G	SOD123	
L1	3.3 nH	0402	
L2	4.7 nH		
L3	560 nH	0603	
R1	1.5 kOhm		
Q1	Transistor ONSEMI FET NTS4101P	SOT323	

Fig 2. Evaluation board includes case, connectors, and components soldered to PCB Note: R1, D3 and Q1 are for reverse voltage protection and may be ommited.

#### **PRODUCT MARKING**



Marking may contain other features or characters for internal lot control

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5 to 1500 MHz 750

#### ADDITIONAL DETAILED TECHNICAL INFORMATION IS AVAILABLE ON OUR DASHBOARD. CLICK HERE

	Data Table
Performance Data	Swept Graphs
	S-Parameter (S2P Files) Data Set (.zip file)
5-200 MHz Operation	See Application Note AN-60-087
Case Style	DF782 (SOT 89) Plastic package, exposed paddle lead finish: tin-silver over nickel
Tape & Reel Standard quantities available on reel	F55
Suggested Layout for PCB Design	PL-477
Evaluation Board	TB-850+ (40-1500 MHz) TB-885+ (5-20 MHz)
Environmental Ratings	ENV08T1

#### **ESD RATING**

Human Body Model (HBM): Class 1A (250<500) in accordance with ANSI/ESD STM 5.1 - 2001 Machine Model (MM): Class class M1 (25V) in accordance with ANSI/ESD STM5.2-1999

#### **MSL RATING**

Moisture Sensitivity: MSL1 in accordance with IPC/JEDEC J-STD-020D

NOTES

- B. Electrical specifications and performance data contained in this specification document are based on Mini-Circuit's applicable established test performance criteria and measurement instructions.
- C. The parts covered by this specification document are subject to Mini-Circuits standard limited warranty and terms and conditions (collectively, "Standard Terms"); Purchasers of this part are entitled to the rights and benefits contained therein. For a full statement of the standard. Terms and the exclusive rights and remedies thereunder, please visit Mini-Circuits' website at www.minicircuits.com/MCLStore/terms.jsp



A. Performance and quality attributes and conditions not expressly stated in this specification document are intended to be excluded and do not form a part of this specification document.